

Part Number

Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Customer supplied material
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Customer supplied material
	4.0	Secondary Flat Orientation	None or SEMI std	Customer supplied material
	5.0	Overall Thickness	332.00 +/- 7.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Edge Chips	0	Bright Light, 100%
	8.0	Bow	0.00 to 0.00	Not measured
	9.0	Warp	0.00 to 0.00	Not measured
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Customer supplied material
	12.0	Handle Orientation	{100} +/- 0.5 degree	Customer supplied material
	13.0	Handle Thickness	270.00 +/- 5.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Customer supplied material
	15.0	Handle Dopant	Boron	Customer supplied material
	16.0	Handle Resistivity	0.001~0.0015 Ohm-cm	Customer supplied material
	17.0	Backside Finish	Polished with lasermark and light handling marks (NO OXIDE)	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 Å	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle	
DeviceSilicon	21.0	Device Growth Method	CZ	Customer supplied material
	22.0	Device Orientation	{100} +/- 0.5 degree	Customer supplied material
	23.0	Nominal Thickness	60.00 +/- 1.00 µm	ADE single point, 100%
	24.0	Distance to device silicon edge from wafer edge	< 2mm	Typical by Process
	25.0	Device Doping Type	P	Customer supplied material
	26.0	Device Dopant	Boron	Customer supplied material
	27.0	Device Resistivity	0.001~0.0015 Ohm-cm	Customer supplied material
	28.0	Surface Voids	None	Bright Light, 100% (note2)
	29.0	Haze	None	Bright Light, 100% (note2)
	30.0	Scratches	none on the front-side	Bright Light, 100% (note2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information